

# SCHOTTKY BARRIER DIODE

## ●Features

Small surface mounting type SC-70/SOT323

Low  $V_F$  and low  $I_R$

High reliability

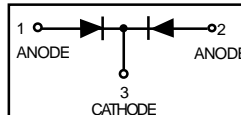
## ●Construction

silicon epitaxial planar

**LRB715T1**



**SC-70/SOT-323**



## MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ )

Parameter	Symbol	Limits	Unit
Peak reverse voltage	$V_{RM}$	40	V
DC reverse voltage	$V_R$	40	V
Mean rectifying current	$I_O$	30	mA
Peak forward surge current	$I_{FSM}$	200	mA
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55~+150	$^\circ\text{C}$

## DEVICE MARKING

LRB715T1=3D

## ELECTRICAL CHARACTERISTICS( $T_A = 25^\circ\text{C}$ )

Parameter	Symbol	Min.	Typ	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	0.37	V	$I_F = 1\text{mA}$
Reverse current	$I_R$	-	-	1	$\mu\text{V}$	$V_R = 10\text{V}$
Capacitance between terminals	$C_T$	-	-	-	V	$V_R = 1\text{V}, f = 1\text{MHz}$

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Electrical characteristic curves( $T_A = 25^\circ\text{C}$ )

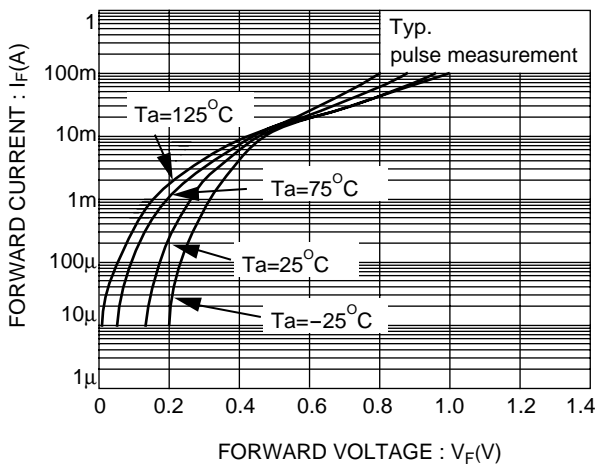


Fig. 1 Forward characteristics

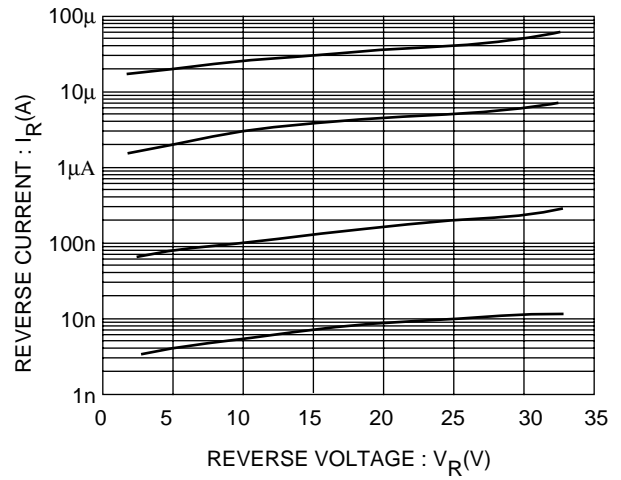


Fig. 2 Reverse characteristics

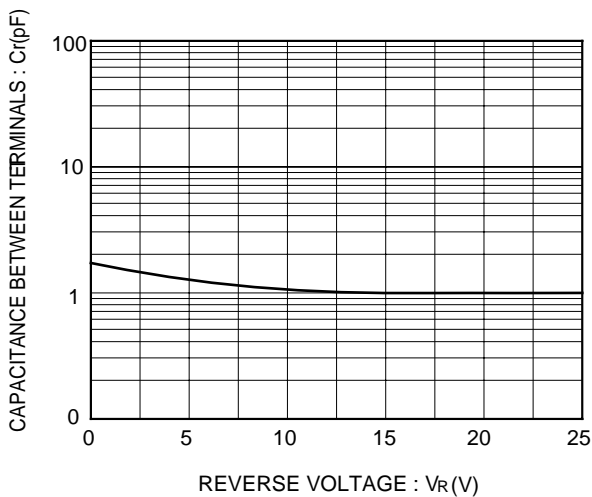


Fig. 3 Capacitance between terminals characteristics

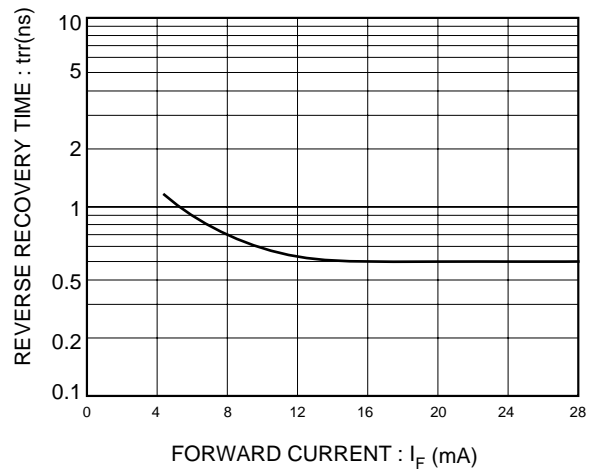


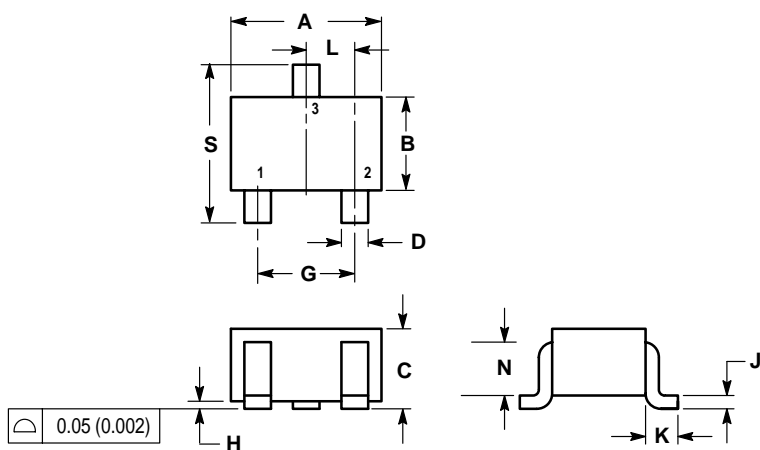
Fig. 4 Reverse recovery time characteristics

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SC-70/SOT-323

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.032	0.040	0.80	1.00
D	0.012	0.016	0.30	0.40
G	0.047	0.055	1.20	1.40
H	0.000	0.004	0.00	0.10
J	0.004	0.010	0.10	0.25
K	0.017REF		0.425REF	
L	0.026BSC		0.650BSC	
N	0.028REF		0.700REF	
S	0.079	0.095	2.00	2.40

- PIN 1. ANODE  
 2. ANODE  
 3. CATHODE

